

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	1	US-20020017685-\$ and undercoat. detx. and gate adj insulating.detx.	US-PGPUB; USPAT; FPRS; EPO; JPO; IBM_TDB	OR	OFF	2007/02/07 12:50
L9	11	(US-20020030228-\$ or US-20040207015-\$ or US-20040211356-\$).did. or (US-5492843-\$ or US-5985704-\$ or US-5310457-\$ or US-4949141-\$ or US-6150203-\$ or US-6794294-\$ or US-5468987-\$).did. or (JP-01128575-\$).did.	US-PGPUB; USPAT; JPO	OR	OFF	2007/02/07 13:36
L10	7	L9 and (poly polysilicon)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2007/02/07 13:36
L11	28129	(a-silicon amorphous adj silicon) and (polysilicon polycrystalline)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2007/02/07 13:36
L12	13024	(a-silicon amorphous adj silicon) near3 (polysilicon polycrystalline)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2007/02/07 13:36
L13	129	(amorphous adj silicon) near (polysilicon polycrystalline) and @pd<"19870101"	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2007/02/07 13:36
L14	7313	(amorphous adj silicon) near (polysilicon polycrystalline)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2007/02/07 13:36
L15	4	(protective adj film cap-layer) with amorphous with thermal adj crystallization	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2007/02/07 13:36
L16	4	(protective adj film cap-layer) with thermal adj crystallization	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2007/02/07 13:36

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L17	17	method near3 (spc solid phase crystallization)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	ADJ	OFF	2007/02/07 13:36
L18	49	("5492843" "5985704") and (over\$1etch\$3 or (buffer with etch\$3))	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	ON	2007/02/07 13:36
L19	195	("5492843" "5985704") and insulat\$3	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	ON	2007/02/07 13:36
L20	166	("5492843" "5985704") and thick\$4 with insulat\$3	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	ON	2007/02/07 13:36
L21	182	("5492843" "5985704") and gate adj insulat\$3	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	ON	2007/02/07 13:36
L22	9	JP-63093150-\$ or JP-61078138-\$ or JP-02031464-\$ or US-6809349-\$ or JP-04096337-\$ or JP-04101432-\$ or JP-02281634-\$ or US-6638825-\$ or JP-01128575-\$	US-PGPUB; USPAT; JPO	OR	ON	2007/02/07 13:36
L23	305	(thin adj film adj transistor or tft) and amorphous adj silicon WITH buffer	USPAT	OR	ON	2007/02/07 13:36
L24	7660	"117"/\$3.ccls.	USPAT	OR	ON	2007/02/07 13:36
L25	4920	(thin adj film adj transistor or tft) and amorphous adj silicon and buffer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/07 13:36
L26	10402	(257/347,350,390,40,51,57,59,66,72). CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2007/02/07 13:36
L27	4831	L26 and (tft thin adj film adj transistor)	US-PGPUB; USPAT	OR	OFF	2007/02/07 13:36
L28	1278	L27 and buffer	US-PGPUB; USPAT	OR	OFF	2007/02/07 13:36
L29	25	"4,767,723"	US-PGPUB; USPAT	OR	ON	2007/02/07 13:36

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L30	913	"5837619" "5492843" (adachi and tft)	US-PGPUB; USPAT	OR	OFF	2007/02/07 13:36
L31	43342	gate insulating and gate electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/02/07 13:36
L32	3347	etch adj rate near4 (sin silicon si)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/02/07 13:36
L33	28129	(a-silicon amorphous adj silicon) and (polysilicon polycrystalline)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2007/02/07 13:36
L34	780	amorphous with thermal adj crystallization	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2007/02/07 13:36
L35	26	"275638"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/02/07 13:36
L36	8153	(Park-Kee\$ or Yoo-J\$ or Han-M\$).in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/07 13:36
L37	4	"275638" and adachi	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/02/07 13:36
L38	21	(buffer near conductive) adj film	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2007/02/07 13:36

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L39	33581	gate adj (insulator insulating insulation insulated insulate oxide) WITH thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/07 13:36
L40	13024	(a-silicon amorphous adj silicon) near3 (polysilicon polycrystalline)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2007/02/07 13:36
L41	23	(thin adj film adj transistor or tft) and amorphous adj silicon and L36	USPAT	OR	ON	2007/02/07 13:36
L42	19	((("6777747") or ("6534788") or ("6528855") or ("6509234") or ("6396079") or ("6033941") or ("5510640") or ("5196717") or ("5173753") or ("5144401") or ("4715930") or ("4287661") or ("4035198") or ("20040173812") or ("20040084722") or ("20040005740") or ("20030122178") or ("20020054247") or ("6746904"))).PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2007/02/07 13:36
L43	8	(L42 or L22) and (hoon near kim or thin adj film adj transistor or tft)	US-PGPUB; USPAT; JPO	OR	ON	2007/02/07 13:36
L44	49	"4851363" not L26	US-PGPUB; USPAT	OR	OFF	2007/02/07 13:36
L45	1559	L25 and "257"/\$3.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/07 13:36
L46	89	L32 and process near4 etching near4 silicon adj nitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/02/07 13:36
L47	17	"5,310,457"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/02/07 13:36

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L48	23	"275,638"	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2007/02/07 13:36
L49	2	(US-20040211356-\$).did. or (US-5985704-\$ or US-4949141-\$).did.	US-PGPUB; USPAT	OR	OFF	2007/02/07 13:36
L50	11	(US-20020030228-\$ or US-20040207015-\$ or US-20040211356-\$).did. or (US-5492843-\$ or US-5985704-\$ or US-5310457-\$ or US-4949141-\$ or US-6150203-\$ or US-6794294-\$ or US-5468987-\$).did. or (JP-01128575-\$).did.	US-PGPUB; USPAT; JPO	OR	OFF	2007/02/07 13:36
L51	4	(protective adj film cap-layer) with amorphous with thermal adj crystallization	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2007/02/07 13:36
L52	4	(protective adj film cap-layer) with thermal adj crystallization	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2007/02/07 13:36
L53	44	amorphous with thermal adj crystallization with thickness	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2007/02/07 13:36
L54	2	L49 and (thick thicker thickest thickened thicken thickness thin thinner) with (oxide nitride insulator insulating insulated)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	ON	2007/02/07 13:36
L55	7	L50 and (poly polysilicon)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2007/02/07 13:36
L56	44	amorphous with thermal adj crystallization with thickness and thickness with (polysilicon silicon)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2007/02/07 13:36
L57	189	hoon near kim	US-PGPUB; USPAT	OR	OFF	2007/02/07 13:36

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L58	7313	(amorphous adj silicon) near (polysilicon polycrystalline)	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2007/02/07 13:36
L59	129	(amorphous adj silicon) near (polysilicon polycrystalline) and @pd<"19870101"	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2007/02/07 13:36
L60	783	(etch etching etchant etched pattern patterned patterning) near4 buffer and (thin adj film adj transistor or tft)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2007/02/07 13:36
L61	4030	L25 and step not step adj for	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/07 13:36
L62	8324	gate (insulation OR dielectric OR oxide) layer.clm.	US-PGPUB; USPAT	ADJ	OFF	2007/02/07 13:36
L63	484447	(thickness OR thick OR thin or thicker OR thinner).clm.	US-PGPUB; USPAT	ADJ	OFF	2007/02/07 13:36
L64	1028778	(step OR overetch).clm.	US-PGPUB; USPAT	ADJ	OFF	2007/02/07 13:36
L65	32227	L63 with L64	US-PGPUB; USPAT	ADJ	OFF	2007/02/07 13:36
L66	467471	(thin film transistor or TFT).clm.	US-PGPUB; USPAT	OR	OFF	2007/02/07 13:36
L67	12927	(thin film transistor or TFT).clm.	US-PGPUB; USPAT	ADJ	OFF	2007/02/07 13:36
L68	2051	L66 with L62	US-PGPUB; USPAT	ADJ	OFF	2007/02/07 13:36
L69	6582	buffer layer.clm.	US-PGPUB; USPAT	ADJ	OFF	2007/02/07 13:36
L70	135	L65 with L69	US-PGPUB; USPAT	ADJ	OFF	2007/02/07 13:36
L71	57	L70 with L66	US-PGPUB; USPAT	ADJ	OFF	2007/02/07 13:36
L72	2	L71 and L68	US-PGPUB; USPAT	ADJ	OFF	2007/02/07 13:36
L73	20941	(activation OR active OR poly OR polysilicon) layer.clm.	US-PGPUB; USPAT	ADJ	OFF	2007/02/07 13:36
L74	135	L70 with L69	US-PGPUB; USPAT	ADJ	OFF	2007/02/07 13:36

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L75	1	L71 with L62	US-PGPUB; USPAT	ADJ	OFF	2007/02/07 13:36
L76	4	"798574".ap.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2007/02/07 13:36
L77	1	L76 AND thickness NEAR3 gate ADJ insulation WITH BUFFER	US-PGPUB; USPAT	OR	OFF	2007/02/07 13:36
L78	1	L76 AND thickness NEAR3 gate ADJ insulation	US-PGPUB; USPAT	OR	OFF	2007/02/07 13:36
L79	3	L76 AND (B1 or thickness NEAR3 gate ADJ insulation WITH BUFFER)	US-PGPUB; USPAT	OR	OFF	2007/02/07 13:36
L80	5	((("2001320062") or ("2002033330")), PN.	JPO; DERWENT	OR	OFF	2007/02/07 13:36
L81	4	L80 not surgical	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/02/07 13:36
L82	4	US-6746901-\$ or US-20020017685-\$ or JP-2002033330-\$	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/02/07 13:36
L83	3	US-6746901-\$ or US-20020017685-\$ or JP-2002033330-\$	US-PGPUB; USPAT; FPRS; EPO; JPO; IBM_TDB	OR	OFF	2007/02/07 13:36
L84	1	US-20020017685-\$ and gate adj insulating adj film.detx.	US-PGPUB; USPAT; FPRS; EPO; JPO; IBM_TDB	OR	OFF	2007/02/07 13:36
L85	1	US-20020017685-\$ and step	US-PGPUB; USPAT; FPRS; EPO; JPO; IBM_TDB	OR	OFF	2007/02/07 13:36
L86	1	US-20020017685-\$ and gate.detx.	US-PGPUB; USPAT; FPRS; EPO; JPO; IBM_TDB	OR	OFF	2007/02/07 13:36

EAST Search History

L87	1	US-20020017685-\$ and undercoat. detx. and step.detx.	US-PGPUB; USPAT; FPRS; EPO; JPO; IBM_TDB	OR	OFF	2007/02/07 13:36
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